NSN 5962-01-371-3180

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View Online at https://aerobasegroup.com/nsn/5962-01-371-3180

view offilite at https://defobasegroup.com/hish/0302-01-071-0100
Maximum Power Dissipation Rating:
2.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bipolar and monolithic and programmed
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes reverse current, dc
Product Name:
Microcircuit, pal, 16-input 8-output and-or invert gate array
Voltage Rating And Type Per Characteristic:
-1.5 volts absolute input and 12.0 volts absolute input
Memory Device Type:
Pal
Hybrid Technology Type:
Monolithic
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883
standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
20 printed circuit
Specification Data:
81349-mil-m-38510/50401brx government specification
Purchase Description Identification:
05869-53218-1
Departure From Cited Designator:

Demilitarization:

Unit Of Measure:

Shelf Life:

N/a

Altered by programming, testing & marking

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